

E.S.D NOISE CLIPPING DIODES

NNCD6.2MF

LOW CAPACITANCE HIGH ESD TYPE ELECTROSTATIC DISCHARGE NOISE CLIPPING DIODES (DUAL TYPE: COMMON ANODE) 3-PIN MINI MOLD

This product is a low capacitance type diode developed for E.S.D. (Electrostatic Discharge) protection. Based on the IEC61000-4-2 test on electromagnetic interference (EMI), the diode assures an endurance of no less than 30 kV, and capacitance is small with 20 pF TYP. This product series is the most suitable for the ESD protection in the high-speed data communication bus such as USB.

NNCD6.2MF include two elements in 3-PIN Mini Mold Package having allowable power dissipation of 200 mW.

FEATURES

- Based on the electrostatic discharge immunity test (IEC61000-4-2), the product assures the minimum endurance of 30 kV.
- Capacitance is small with 20 pF TYP. (at VR = 0 V, f = 1 MHz). It is excellent in the frequency characteristic.

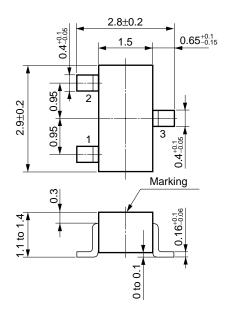
APPLICATIONS

 External interface circuit E.S.D. protection in the high-speed data communication bus such as USB.

MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Power Dissipation P 200 mW (Total) Surge Reverse Power PRSM 2 W (t = 10 μ s 1 pulse) Fig.5 Junction Temperature T_j 150°C Storage Temperature T_{stg} -55°C to +150°C

PACKAGE DIMENSIONS (in millimeters)

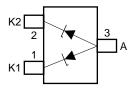


PIN CONNECTION

1. K1 : Cathode 1 SC-59 (EIAJ)

2. K2 : Cathode 2

3. A : Anode (common)



The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

ELECTRICAL CHARACTERISTICS (TA = 25°C) (A-K1, A-K2)

Type No.	Breakdown Voltage ^{Note 1} VBR (V)			Dynamic ^{Note 2} Impedance Zz (Ω)		Reverse Leakage I _R (μA)		Capacitance Cւ (pF)		E.S.D Voltage (kV)	
	MIN.	MAX.	Iτ (mA)	MAX.	Iτ (mA)	MAX.	V _R (V)	TYP.	TEST CONDITION	MIN.	TEST CONDITION
NNCD6.2MF	5.7	6.7	5	50	5	2	3.0	20	V _R = 0 V f = 1 MHz	30	C = 150 pF $R = 330 \Omega$ (IEC61000-4-2)

Note 1. Tested with pulse (40 ms)

2. Zz is measured at IT give a small A.C. signal.

TYPICAL CHARACTERISTICS (T_A = 25°C)

Fig. 1 POWER DISSIPATION vs.

AMBIENT TEMPERATURE

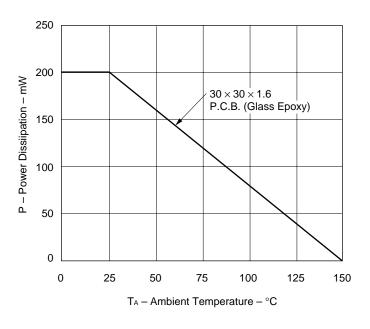
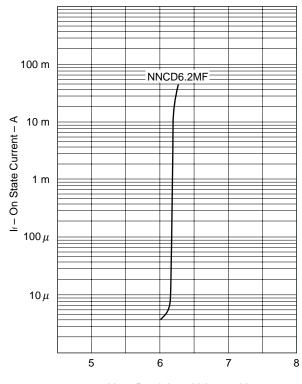


Fig. 2 It vs. V_{BR} CHARACTERISTICS



V_{BR} - Breakdown Voltage - V

Fig. 3 Ct-VR CHARACTERISTICS

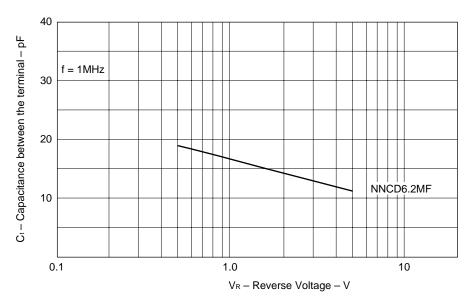


Fig. 4 TRANSIENT THERMAL IMPEADANCE CHARACTERISTIC

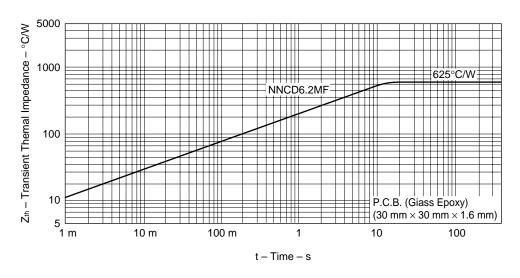
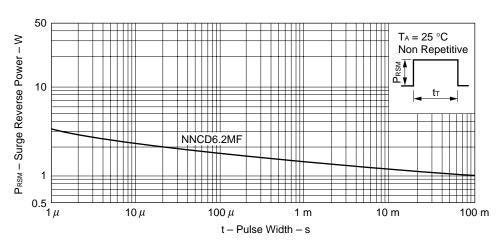


Fig. 5 SURGE REVERSE POWER RATINGS



3

[MEMO]

- The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.
- No part of this document may be copied or reproduced in any form or by any means without the prior written
 consent of NEC Corporation. NEC Corporation assumes no responsibility for any errors which may appear in
 this document.
- NEC Corporation does not assume any liability for infringement of patents, copyrights or other intellectual property
 rights of third parties by or arising from use of a device described herein or any other liability arising from use
 of such device. No license, either express, implied or otherwise, is granted under any patents, copyrights or other
 intellectual property rights of NEC Corporation or others.
- Descriptions of circuits, software, and other related information in this document are provided for illustrative purposes in semiconductor product operation and application examples. The incorporation of these circuits, software, and information in the design of the customer's equipment shall be done under the full responsibility of the customer. NEC Corporation assumes no responsibility for any losses incurred by the customer or third parties arising from the use of these circuits, software, and information.
- While NEC Corporation has been making continuous effort to enhance the reliability of its semiconductor devices, the possibility of defects cannot be eliminated entirely. To minimize risks of damage or injury to persons or property arising from a defect in an NEC semiconductor device, customers must incorporate sufficient safety measures in its design, such as redundancy, fire-containment, and anti-failure features.
- NEC devices are classified into the following three quality grades:
 - "Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.
 - Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
 - Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
 - Specific: Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.

M7 98.8

This datasheet has been download from:

www.datasheetcatalog.com

Datasheets for electronics components.